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(54) **Title:** LOW RESISTIVITY DRAM BURIED WORD LINE STACK

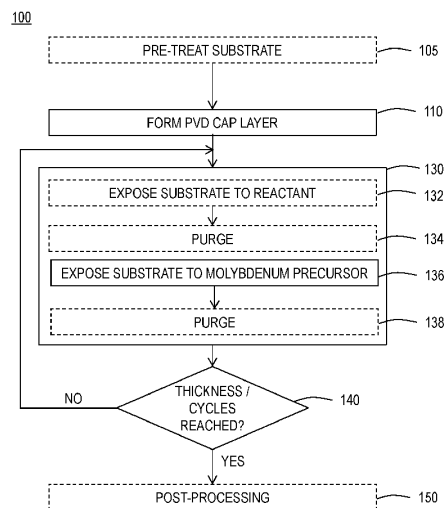


FIG. 1

(57) **Abstract:** Methods for DRAM device with a buried word line are described. The method includes forming a metal cap layer and a molybdenum conductor layer in a feature on a substrate. The method includes depositing the metal cap layer on the substrate by physical vapor deposition (PVD) and depositing the molybdenum conductor layer by atomic layer deposition (ALD) on the metal cap layer.

[Continued on next page]

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